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December 2013

# FQAF11N90C

# N-Channel QFET® MOSFET

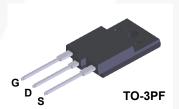
900 V, 7.0 A, 1.1 Ω

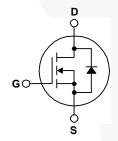
# **Description**

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

### **Features**

- 7.0 A, 900 V,  $R_{DS(on)}$  = 1.1  $\Omega$  (Max.) @  $V_{GS}$  = 10 V,  $I_{D}$  = 3.5 A
- Low Gate Charge (Typ. 60 nC)
- · Low Crss (Typ. 23 pF)
- 100% Avalanche Tested





# Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter		FQAF11N90C	Unit	
V <sub>DSS</sub>	Drain-Source Voltage		900	V	
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C)		7.0	Α	
	- Continuous (T <sub>C</sub> = 100°C)		4.4	Α	
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	28.0	Α	
V <sub>GSS</sub>	Gate-Source Voltage		± 30	V	
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)		960	mJ	
I <sub>AR</sub>	Avalanche Current	(Note 1)	7.0	Α	
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	12	mJ	
dv/dt	Peak Diode Recovery dv/dt (Note 3)		4.0	V/ns	
$P_D$	Power Dissipation (T <sub>C</sub> = 25°C)		120	W	
	- Derate above 25°C		0.96	W/°C	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150	°C	
T <sub>L</sub>	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds.		300	°C	

# **Thermal Characteristics**

Symbol	Parameter	FQAF11N90C	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	1.04	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W	

# **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQAF11N90C	FQAF11N90C	TO-3PF	Tube	N/A	N/A	30 units

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Uni
Off Cha	racteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	900			V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C		1.0		V/°
I <sub>DSS</sub>	Zara Cata Valtaga Drain Current	V <sub>DS</sub> = 900 V, V <sub>GS</sub> = 0 V			10	μΑ
	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 720 V, T <sub>C</sub> = 125°C		-	100	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V		-	100	n/
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -30 V, V <sub>DS</sub> = 0 V		1	-100	n/
On Cha	racteristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	3.0		5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10 V, I <sub>D</sub> =3.5 A		0.91	1.1	Ω
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 50 V, I <sub>D</sub> = 3.5 A				S
<b>Dynam</b> i C <sub>iss</sub>	ic Characteristics Input Capacitance	I		2530	3290	pF
Coss	Output Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$		215	280	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f = 1.0 MHz		23	30	pF
	ng Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 450 V, I <sub>D</sub> = 11.0 A,		60	130	ns
t <sub>r</sub>	Turn-On Rise Time	$R_{G} = 25 \Omega$		130	270	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	_		130	270	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)		85	180	ns
Qg	Total Gate Charge	V <sub>DS</sub> = 720 V, I <sub>D</sub> = 11.0 A,		60	80	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 10 V		13		nC
Q <sub>gd</sub>	Gate-Drain Charge	(Note 4)		25		nC
Drain-S	ource Diode Characteristics ar	nd Maximum Ratings				
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current				7.0	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode F				28.0	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 7.0 A			1.4	V

 $t_{rr}$ 

 $Q_{rr}$ 

Reverse Recovery Time

Reverse Recovery Charge

ns

μC

1000

17.0

 $V_{GS} = 0 V, I_S = 11.0 A,$ 

 $dI_F / dt = 100 A/\mu s$ 

Notes: 1. Repetitive rating : pulse-width limited by maximum junction temperature. 2. L = 37 mH, I<sub>AS</sub> = 7.0 A, V<sub>DD</sub> = 50 V, R<sub>G</sub> = 25  $\Omega$ , starting T<sub>J</sub> = 25°C . 3. I<sub>SD</sub>  $\leq$  11.0 A, di/dt  $\leq$  200 A/ $\mu$ s, V<sub>DD</sub>  $\leq$  BV<sub>DSS</sub>, starting T<sub>J</sub> = 25°C. 4. Essentially independent of operating temperature.

# **Typical Characteristics**

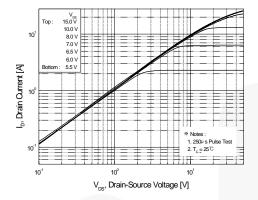


Figure 1. On-Region Characteristics

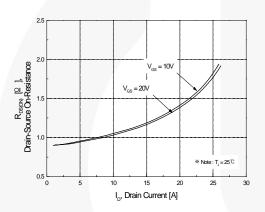


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

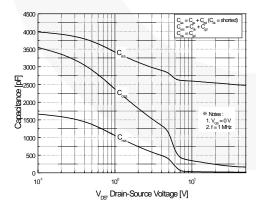


Figure 5. Capacitance Characteristics

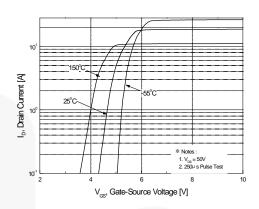


Figure 2. Transfer Characteristics

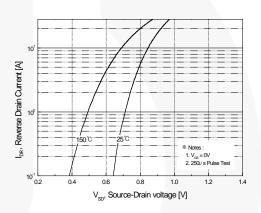


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

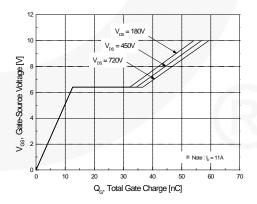
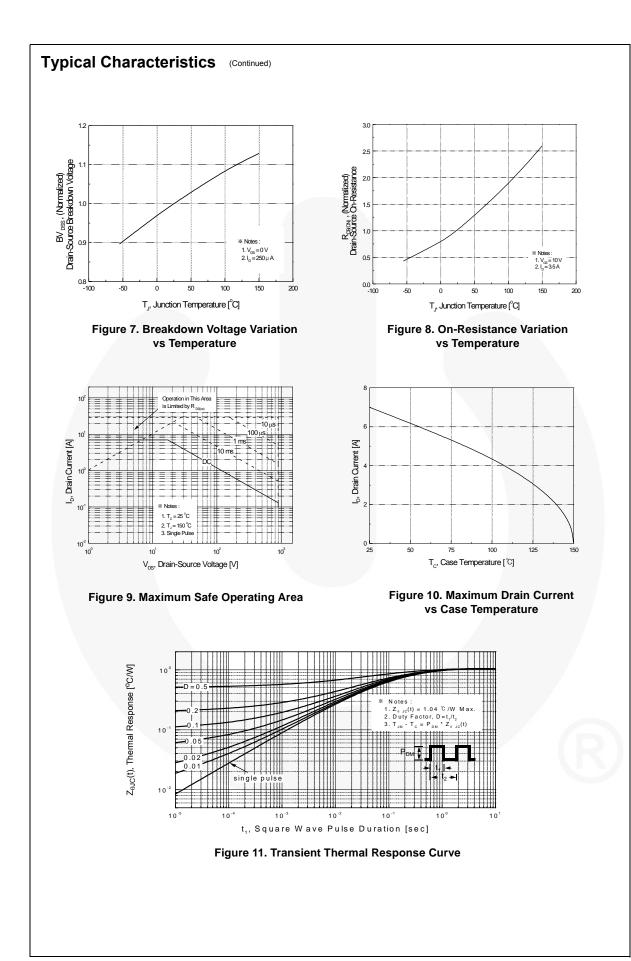


Figure 6. Gate Charge Characteristics



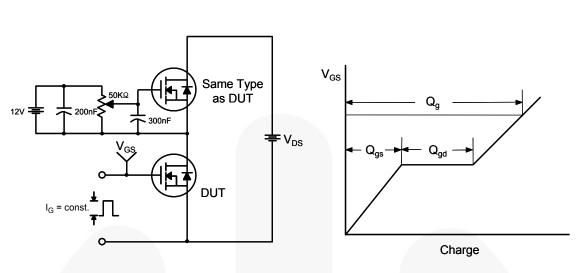


Figure 12. Gate Charge Test Circuit & Waveform

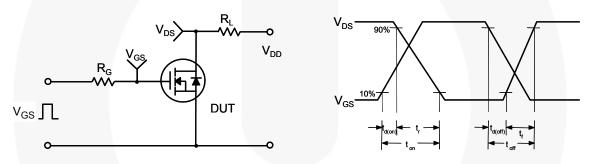


Figure 13. Resistive Switching Test Circuit & Waveforms

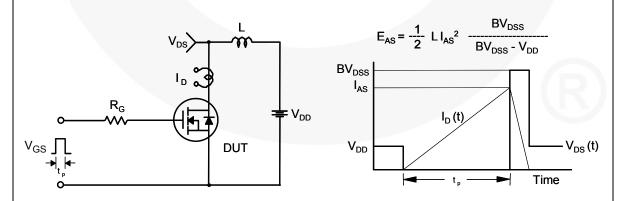
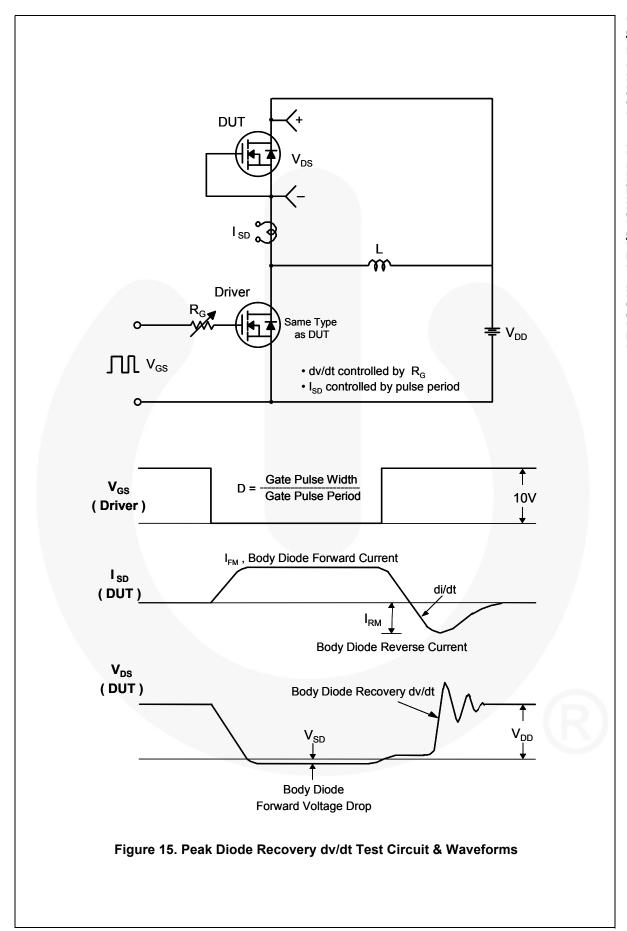


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



# **Mechanical Dimensions**

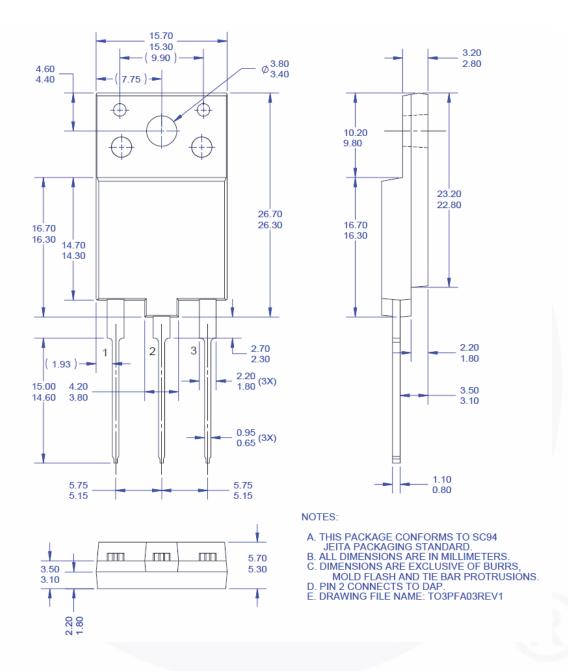


Figure 16. TO3PF, Molded, 3-Lead, Full Pack (AG)

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